

Abstract of the Disclosure

A semiconductor device has a semiconductor substrate 1; a first interlayer insulating film 2 formed on the semiconductor substrate, and having first contact holes; first contact plugs 12 and 13 formed on the first interlayer insulating film 2 and having portions buried in the first contact holes and portions protruded from the surface of the first interlayer insulating film 2; sidewalls 15 formed on the sides of the protruded portions of the first contact plugs 12 and 13; a second interlayer insulating film 16 formed on the first interlayer insulating film 2 the first contact plugs 12 and 13 and the sidewalls 15, and having second contact holes; and second contact plugs 19 and 20 formed on the second contact holes, and connected to the first contact plugs 12 and 13.